BTA208-800F



3Q Hi-Com Triac
Rev. 06 — 12 April 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package. This "series F" triac balances the requirements of commutation performance and gate sensitivity. The "less sensitive gate" "series F" is intended for interfacing with low power drivers, including microcontrollers in higher "noise" environments.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Good immunity to false turn-on by dV/dt
- High commutation capability with less sensitive gate
- High voltage capability
- Less sensitive gate suitable for higher "noise" environment applications
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

Electronic thermostats

General purpose motor controls

1.4 Quick reference data

Table 1. Quick reference data

$V_{DRM} \qquad \begin{array}{c} \text{repetitive peak} \\ \text{off-state voltage} \end{array} \qquad \begin{array}{c} - \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
on-state current $t_{p} = 20 \text{ ms; see } \frac{\text{Figure 4};}{\text{see } \text{Figure 5}}$ $I_{T(RMS)} \text{RMS on-state current} \text{full sine wave; } T_{mb} \leq 102 ^{\circ}\text{C}; - - 8 \text{A}$ $\text{see } \frac{\text{Figure 1}}{\text{see } \text{Figure 2}}; \text{ see } \frac{\text{Figure 2}}{\text{see } \text{Figure 2}};$ $\text{Static characteristics}$ $I_{GT} \text{gate trigger current} \begin{array}{c} V_{D} = 12 \text{V; } I_{T} = 0.1 \text{A; } T2 + \text{G+;} - - 25 \text{mA} \\ \hline I_{j} = 25 ^{\circ}\text{C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ \hline V_{D} = 12 \text{V; } I_{T} = 0.1 \text{A; } T2 + \text{G-;} - - 25 \text{mA} \\ \hline I_{j} = 25 ^{\circ}\text{C; see } \frac{\text{Figure 7}}{\text{Figure 7}} \\ \hline V_{D} = 12 \text{V; } I_{T} = 0.1 \text{A; } T2 - \text{G-;} - - 25 \text{mA} \\ \hline \end{array}$	V_{DRM}	•		-	-	800	V
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	I _{TSM}	•	$t_p = 20 \text{ ms}$; see Figure 4;	-	-	65	Α
$\begin{array}{c} I_{GT} & \text{gate trigger current} \\ V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 + G+; \\ T_j = 25 \ ^{\circ}\text{C; see} \ \frac{\text{Figure 7}}{\text{Figure 7}} \\ \hline V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 + G-; \\ T_j = 25 \ ^{\circ}\text{C; see} \ \frac{\text{Figure 7}}{\text{Figure 7}} \\ \hline V_D = 12 \ \text{V; } I_T = 0.1 \ \text{A; } T2 - G-; \\ \hline \end{array} \qquad - \qquad 25 \qquad \text{mA} \\ \hline \end{array}$	I _{T(RMS)}	RMS on-state current	see Figure 1; see Figure 2;	-	-	8	Α
$T_{j} = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{V}_{D}} = 12 \text{ V; } I_{T} = 0.1 \text{ A; } T2 + \text{G-;} \qquad - \qquad 25 \qquad \text{mA}$ $T_{j} = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{V}_{D}} = 12 \text{ V; } I_{T} = 0.1 \text{ A; } T2 - \text{G-;} \qquad - \qquad 25 \qquad \text{mA}$	Static cha	racteristics					
$T_j = 25 ^{\circ}\text{C}$; see Figure 7 $V_D = 12 \text{V}$; $I_T = 0.1 \text{A}$; T2- G-; - 25 mA	I _{GT}	gate trigger current		-	-	25	mA
D , 1 - , - ,				-	-	25	mA
I _j = 25 °C; see <u>Figure 7</u>			$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2\text{- G-}; $ $T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure 7}}{}$	-	-	25	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		. .
2	T2	main terminal 2	mb	T2—T1
3	G	gate		sym051
mb	T2	mounting base; connected to main terminal 2		
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

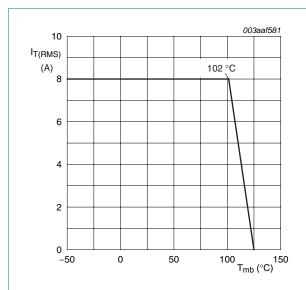
Type number	Package		
	Name	Description	Version
BTA208-800F	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

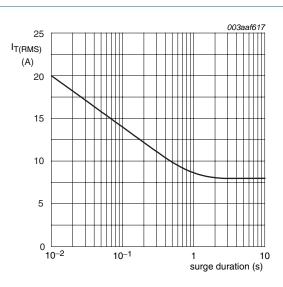
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T _{mb} ≤ 102 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	65	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	71	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	21	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 12 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	125	°C

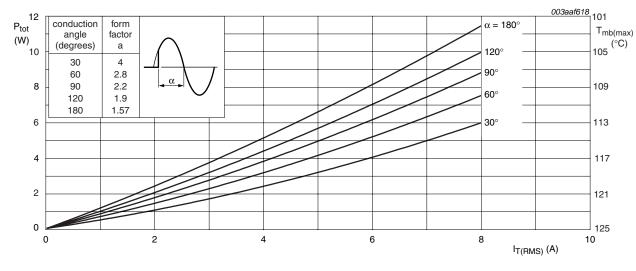




 $f = 50 \text{ Hz}; T_{mb} = 102 \,{}^{\circ}C$

Fig 1. RMS on-state current as a function of heatsink temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum value



 α = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

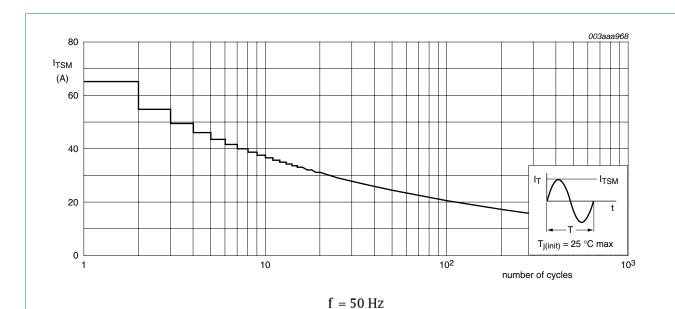


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

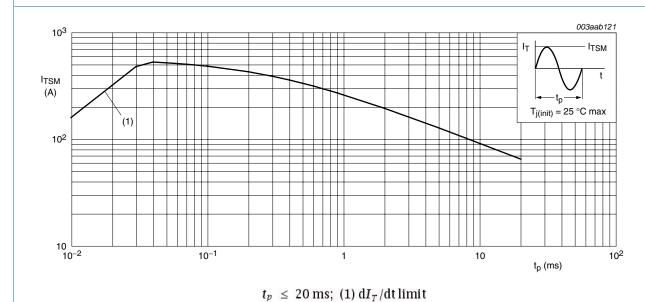


Fig 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	2	K/W
		half cycle; see Figure 6	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

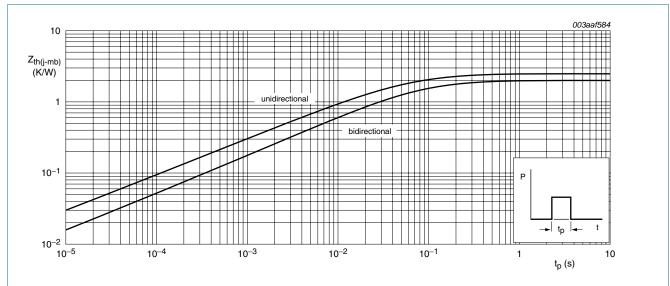
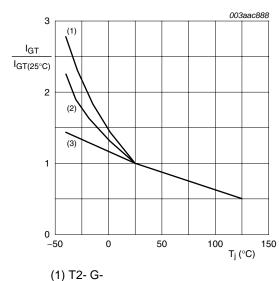


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+G+; T_j = 25 ^{\circ}\text{C};$ see Figure 7	-	-	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 7	-	-	25	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-}; T_j = 25 ^{\circ}\text{C};$ see Figure 7	-	-	25	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{ Composition}}$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-; T_j = 25 ^{\circ}\text{C};$ see Figure 8	-	-	30	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } T_j}$	-	-	30	mΑ
V_{T}	on-state voltage	$I_T = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{}$	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C}$	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 \text{ °C}$	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; exponential waveform; gate open circuit	70	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 8 A; dV_{com}/dt = 0.1 V/µs; gate open circuit; see Figure 12	20	-	-	A/m
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 8 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit};$ see Figure 12	14	-	-	A/m



- (2) T2+ G-
- (3) T2+ G+

Normalized gate trigger current as a function of Fig 7. junction temperature

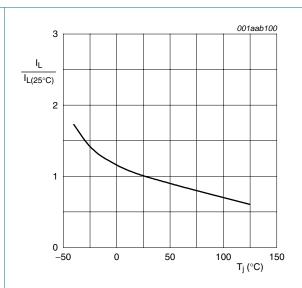
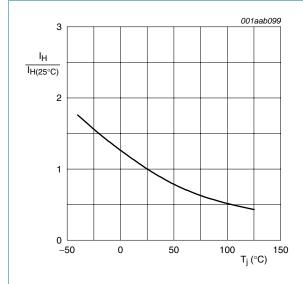
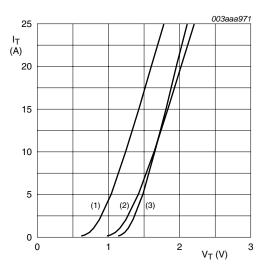


Fig 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of Fig 9. junction temperature



Vo = 1.264 V; Rs = 0.0378 Ω

- (1) Tj = 125 °C; typical values
- (2) Tj = 125 °C; maximum values
- (3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

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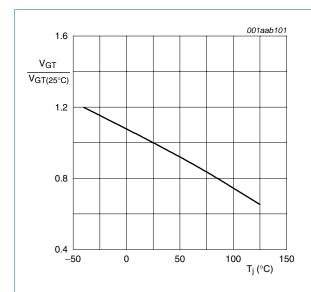


Fig 11. Normalized gate trigger voltage as a function of junction temperature

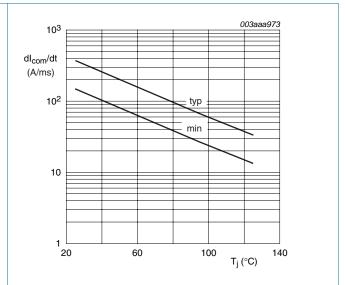
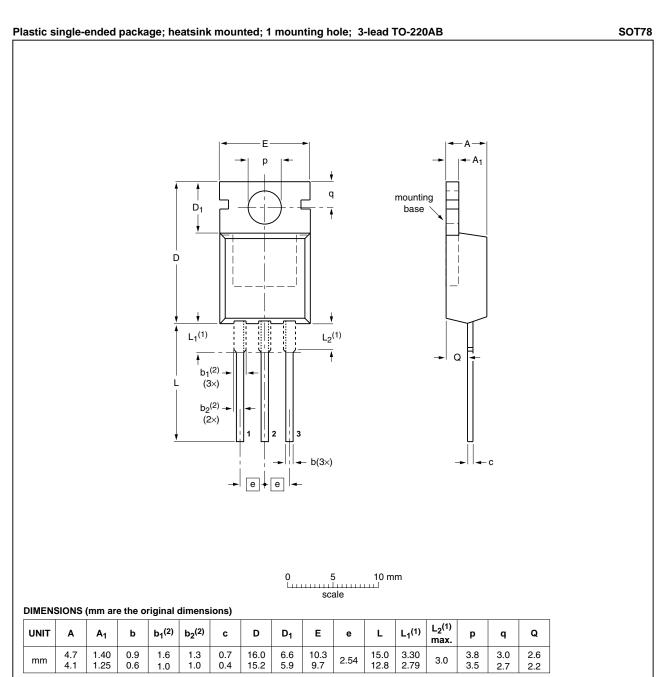


Fig 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DA	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 13. Package outline SOT78 (TO-220AB)

BTA208-800F

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208-800F v.6	20110412	Product data sheet	-	BTA208-800F v.5
Modifications: • Various changes to content.				
BTA208-800F v.5	20101123	Product data sheet	-	BTA208_SERIES_D_E_F v.4

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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3Q Hi-Com Triac

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